EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L6	5387	((257/59) or (257/72) or (257/764) or (257/765) or (257/770) or (257/771)).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/04/01 23:36
L7	1390	6 AND TFT and Source and data and gate and insulating and pixel and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:37
L8	1062	6 AND TFT and Source and data and gate and insulating and pixel and electrode and (Chromium Aluminum Molybdenum)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:38
L9	564	6 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:39
L10	255	9 and @ad<"20020115"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:38
L11	255	9 and @ad<"20020115"	US-PGPUB; USPAT	OR	ON	2007/04/01 23:38
L12	286	6 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:39
L13	267	6 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation and (SiNx SiN nitride)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:40

L14	193	6 AND TFT and Source and insulating and pixel and (Chromium Aluminum Molybdenum) and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode)) and passivation and (SiNx SiN nitride) and organic	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 23:40
S1	2	"20050173732"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 02:42
S2	8466	TFT and pixel and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 02:44
S3	3086	TFT and pixel and (gate near (line pad wire electrode)) and (data near (line pad wire electrode)) and ((source drain) near (line pad wire electrode))	USPAT	OR	ON	2007/04/01 02:44
S4	2156	S3 and oxide and (Cr$3 Mo$3 Al$3)	USPAT	OR	ON	2007/04/01 02:46
S5	1453	S3 and oxide and (Chromium Aluminum Molybdenum)	USPAT	OR	ON	2007/04/01 02:47
S6	862	S5 and @ad<"20020115"	USPAT	OR	ON	2007/04/01 02:47
S7	96	S6 and (low near resistivity)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:34
S12	6	"5905589"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:20
S13	32	"5062689"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/04/01 03:20